

BITLINE OF SEMICONDUCTOR DEVICE HAVING STUD TYPE CAPPING LAYER
AND METHOD FOR FABRICATING THE SAME

ABSTRACT OF THE DISCLOSURE

5 A semiconductor device with a bitline structure has a stud type capping layer. A method of fabricating the same achieves sufficient process margins and reduces parasitic capacitance.

 The device may include an insulating film formed on a semiconductor substrate and having a bitline contact and a groove-shaped bitline pattern, a bitline formed on the bitline
10 contact and on a portion of the bitline pattern and that is surrounded by the insulating film, and a bitline capping layer formed on the bitline within the bitline pattern and the insulating film that protrudes from the insulating film. A protruded portion of the bitline capping layer is wider than a width of the bitline.